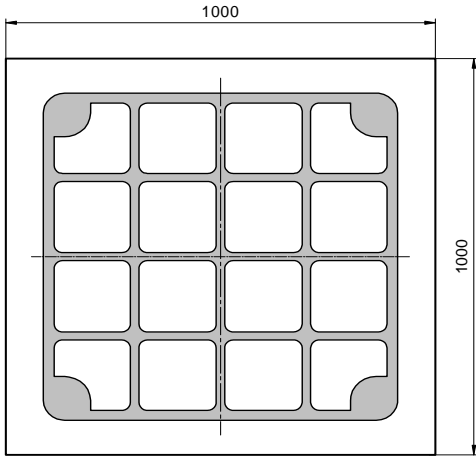


Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	N (cathode) up

 <p>PoC-05</p>	typ. dimensions (µm)
	<p><u>typ. thickness</u> 160 (±25) µm</p> <p><u>cathode</u> gold alloy, 1.5 µm</p> <p><u>anode</u> gold alloy, 0.5 µm structured, 25% covered</p>

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.3	1.5	V
Forward voltage ¹	$I_F = 350 \text{ mA}$	V_F		1.5	1.8	V
Reverse voltage	$I_R = 100 \text{ µA}$	V_R	5			V
Radiant power	$I_F = 20 \text{ mA}$	Φ_e	3.5	5		mW
Radiant power ¹	$I_F = 350 \text{ mA}$	Φ_e	70	90		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_P	860	870	880	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		35		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		20		ns

¹Measured on bare chip glued on a $\varnothing 8 \times 1 \text{ mm}$ Cu header with *EPIGAP* equipment

Labeling

Type	Lot	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	$\lambda_P(\text{typ})$ [nm]	Quantity
ELC-870-21					

Packing: Chips on adhesive film with wire-bond side on top